Peng Dong

List of Publications by Year
in descending order

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25	224	1163117 8	996975 15
papers	citations	h-index	g-index

25	25	25	150
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Synergistic effects of bithiophene ammonium salt for high-performance perovskite solar cells. Journal of Materials Chemistry A, 2022, 10, 9971-9980.	10.3	14
2	Light-induced beneficial ion accumulation for high-performance quasi-2D perovskite solar cells. Energy and Environmental Science, 2022, 15, 2499-2507.	30.8	18
3	Relating Gain Degradation to Defects Production in Neutron-Irradiated 4H-SiC Transistors. IEEE Transactions on Nuclear Science, 2021, 68, 312-317.	2.0	6
4	Atomistic Mechanism of 4 H - <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:mrow><mml:mi>Si</mml:mi><mml:mi mathvariant="normal">C</mml:mi></mml:mrow><mml:mo>/</mml:mo><mml:msub><mml:mrow><mml:mi>Si</mml:mi><mml:mi mathvariant="normal">O</mml:mi></mml:mrow><mml:mn>2</mml:mn></mml:msub></mml:math> Interface Carrier-Trapping Effects on Breakdown-Voltage Degradation in Power Devices. Physical Review Applied, 2021, 15, .	3.8	7
5	Electronic and doping properties of hexagonal silicon carbide with stacking faults induced cubic inclusions. Journal of Applied Physics, 2021, 129, .	2.5	2
6	Understanding the Influence of Cation and Anion Migration on Mixedâ€Composition Perovskite Solar Cells via Transient Ion Drift. Physica Status Solidi - Rapid Research Letters, 2021, 15, 2100225.	2.4	8
7	Effect of Ultraviolet Irradiation on 4H-SiC PiN Diodes Characteristics. Nanoscale Research Letters, 2021, 16, 141.	5.7	1
8	Influence of ion implantation and high temperature Ar annealing on carrier lifetime in n-type 4H-SiC epilayers. , 2020, , .		0
9	Effects of Neutron Irradiation on the Static and Switching Characteristics of High-Voltage 4H-SiC p-type Gate Turn-off Thyristors. IEEE Transactions on Electron Devices, 2019, 66, 3910-3915.	3.0	5
10	Optimized phosphorus diffusion process and performance improvement of c-Si solar cell by eliminating SiP precipitates in the emitter. Journal of Materials Science: Materials in Electronics, 2019, 30, 13820-13825.	2.2	3
11	Electron Radiation Effects on the 4H-SiC PiN Diodes Characteristics: An Insight From Point Defects to Electrical Degradation. IEEE Access, 2019, 7, 170385-170391.	4.2	8
12	Forward Voltage Drop Induced by an Abnormal Threading Dislocation Aggregation in 4H-SiC GTO Devices. Materials, 2019, 12, 4042.	2.9	1
13	Study of gamma-ray radiation effects on the passivation properties of atomic layer deposited Al2O3 on silicon using deep-level transient spectroscopy. Journal of Materials Science: Materials in Electronics, 2019, 30, 1148-1152.	2.2	6
14	Studies of annealing of point defects and their influence on the electrical degradation and recovery behaviors of heavily neutron irradiated silicon. Radiation Effects and Defects in Solids, 2018, 173, 1018-1026.	1.2	1
15	Effect of Germanium Doping on the Production and Evolution of Divacancy Complexes in Neutron Irradiated Czochralski Silicon. Journal of Electronic Materials, 2018, 47, 5019-5024.	2.2	2
16	Sample thickness effect of thermal vibration correction within X-ray dynamical theory for germanium-doped silicon. Journal of Applied Physics, 2017, 121, 125704.	2.5	7
17	Effect of germanium doping on the formation kinetics of vacancy-dioxygen complexes in high dose neutron irradiated crystalline silicon. Journal of Applied Physics, 2017, 122, 095704.	2.5	4
18	Carbon effect on the survival of vacancies in Czochralski silicon during rapid thermal anneal. Journal of Applied Physics, 2017, 122, 045705.	2.5	1

#	Article	IF	Citations
19	Boron deactivation in heavily boron-doped Czochralski silicon during rapid thermal anneal: Atomic level understanding. Applied Physics Letters, 2014, 104, 032102.	3.3	2
20	Enhanced internal gettering in n/n+ epitaxial silicon wafer: coaction of nitrogen impurity and vacancy on oxygen precipitation in substrate. Journal of Materials Science: Materials in Electronics, 2014, 25, 3486-3491.	2.2	1
21	Impurity engineering of Czochralski silicon. Materials Science and Engineering Reports, 2013, 74, 1-33.	31.8	52
22	Quantitative Study of the Evolution of Oxygen and Vacancy Complexes in Czochralski Silicon. Applied Physics Express, 2012, 5, 021302.	2.4	6
23	Germanium-doped Czochralski silicon for photovoltaic applications. Solar Energy Materials and Solar Cells, 2011, 95, 2466-2470.	6.2	24
24	Effect of germanium on the kinetics of boron-oxygen defect generation and dissociation in Czochralski silicon. Applied Physics Letters, 2010, 97, 162107.	3.3	12
25	Germanium effect on oxygen precipitation in Czochralski silicon. Journal of Applied Physics, 2004, 96, 4161-4165.	2.5	33